SKM1000GB17E4

SEMITRANS® 10

IGBT4 Modules

SKM1000GB17E4

Features*

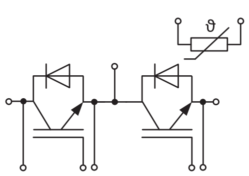
- Symmetrical current sharing
- Low-inductive module design
- High mechanical robustness
- UL recognized, file no. E63532

Typical Applications

- Motor Drives
- UPS Systems
- Solar Inverters

Remarks

Recommended T_{jop} = -40 ... +150°C
I_{DC} ≤ 1000A for $T_{Terminal}$ = 100°C



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Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
IGBT				
V_{CES}	T_j = 25 °C		1700	V
I_C	T_j = 175 °C	T_c = 25 °C	1300	A
		T_c = 100 °C	850	A
I_{Cnom}			1000	A
I_{CRM}			2000	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 1000 V V_{GE} ≤ 15 V V_{CES} ≤ 1700 V	T_j = 150 °C	10	µs
T_j			-40 ... 175	°C
Inverse diode				
V_{RRM}	T_j = 25 °C		1700	V
I_F	T_j = 175 °C	T_c = 25 °C	1427	A
		T_c = 100 °C	890	A
I_{FRM}			2000	A
I_{FSM}	t_p = 10 ms, sin 180°, T_j = 25 °C		6240	A
T_j			-40 ... 175	°C
Module				
$I_{t(RMS)}$			1000	A
T_{stg}			-40 ... 150	°C
V_{isol}	AC sinus 50 Hz, t = 1 min		4000	V

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
$V_{CE(sat)}$	I_C = 1000 A V_{GE} = 15 V chiplevel	T_j = 25 °C		1.99	2.31	V
		T_j = 150 °C		2.44	2.77	V
V_{CE0}	chiplevel	T_j = 25 °C		1.10	1.20	V
		T_j = 150 °C		1.00	1.10	V
r_{CE}	V_{GE} = 15 V chiplevel	T_j = 25 °C		0.89	1.11	mΩ
		T_j = 150 °C		1.44	1.67	mΩ
$V_{GE(th)}$	V_{GE}=V_{CE}, I_C = 36 mA		5.2	5.8	6.4	V
I_{CES}	V_{GE} = 0 V, V_{CE} = 1700 V, T_j = 25 °C				5	mA
C_{ies}	V_{CE} = 25 V V_{GE} = 0 V	f = 1 MHz		70.8		nF
C_{oes}		f = 1 MHz		2.58		nF
C_{res}		f = 1 MHz		2.28		nF
Q_G	V_{GE} = +15V / -15 V			7200		nC
R_{Gint}	T_j = 25 °C			1.5		Ω
$t_{d(on)}$	V_{CC} = 900 V I_C = 1000 A V_{GE} = +15/-15 V $R_{G\,on}$ = 1.2 Ω $R_{G\,off}$ = 1.2 Ω di/dt_{on} = 8.2 kA/µs di/dt_{off} = 4.7 kA/µs dv/dt = 3800 V/µs L_s = 25 nH	T_j = 150 °C		730		ns
t_r		T_j = 150 °C		115		ns
E_{on}		T_j = 150 °C		450		mJ
$t_{d(off)}$		T_j = 150 °C		990		ns
t_f		T_j = 150 °C		175		ns
E_{off}		T_j = 150 °C		370		mJ
$R_{th(j-c)}$	per IGBT				0.034	K/W
$R_{th(c-s)}$	per IGBT (λ_{grease}=0.81 W/(m*K))			0.016		K/W
$R_{th(c-s)}$	per IGBT, pre-applied phase change material			0.013		K/W

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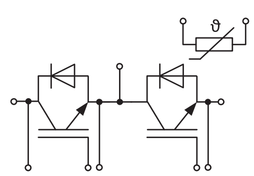

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Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	I_F = 1000 A V_{GE} = 0 V chiplevel	T_j = 25 °C		1.78	2.12	V
		T_j = 150 °C		1.81	2.14	V
V_{F0}	chiplevel	T_j = 25 °C		1.32	1.56	V
		T_j = 150 °C		1.08	1.22	V
r_F	chiplevel	T_j = 25 °C		0.46	0.56	mΩ
		T_j = 150 °C		0.73	0.92	mΩ
I_{RRM}	I_F = 1000 A di/dt_{off} = 8.38 kA/µs V_{GE} = -15 V V_{CC} = 900 V	T_j = 150 °C		800		A
Q_{rr}		T_j = 150 °C		360		µC
E_{rr}		T_j = 150 °C		200		mJ
$R_{th(j-c)}$	per diode				0.043	K/W
$R_{th(c-s)}$	per diode (λ_{grease}=0.81 W/(m*K))			0.017		K/W
$R_{th(c-s)}$	per diode, pre-applied phase change material			0.014		K/W
Module						
L_{CE}				10		nH
$R_{CC'+EE'}$	measured per switch, T_C = 25 °C			0.2		mΩ
$R_{th(c-s)1}$	calculated without thermal coupling (λ_{grease}=0.81 W/(m*K))			0.0041		K/W
$R_{th(c-s)2}$	including thermal coupling, T_s underneath module (λ_{grease}=0.81 W/(m*K))			0.007		K/W
$R_{th(c-s)2}$	including thermal coupling, T_s underneath module, pre-applied phase change material			-		K/W
M_s	to heat sink M5		4		6	Nm
M_t		to terminals M8	8		10	Nm
		to terminals M4	1.8		2.1	Nm
w					1250	g
Temperature Sensor						
R_{100}	T_c=100°C (R_{25}=5 kΩ)			493 ± 5%		Ω
$B_{100/125}$	$R_{(T)}=R_{100}exp[B_{100/125}(1/T-1/T_{100})]$; T[K];			3550 ±2%		K

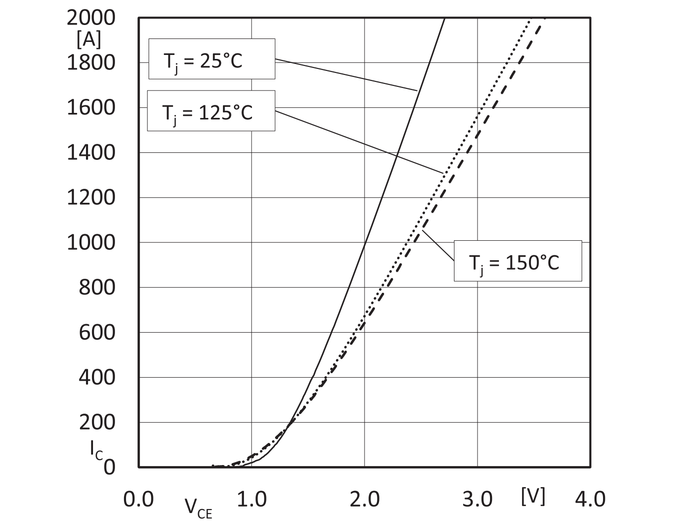


Fig. 1: Output characteristics IGBT (typical); $I_C = f(V_{CE})$; V_{GE} = 15V; (chiplevel)

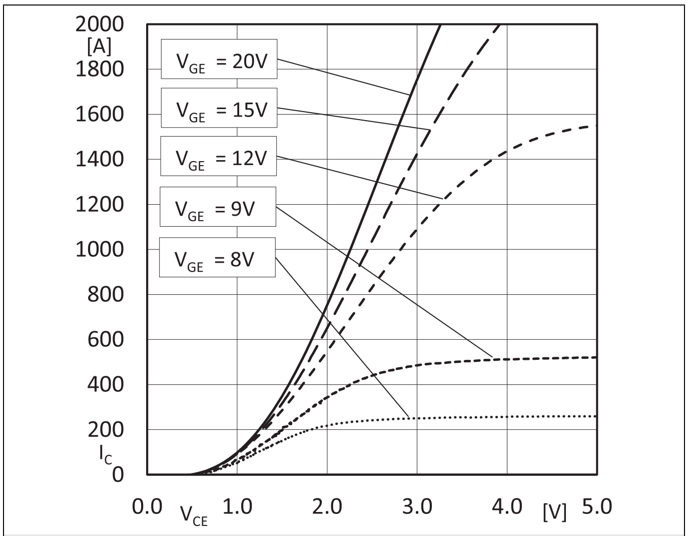


Fig. 2: Output characteristics IGBT (typical); $I_C = f(V_{CE})$; T_j = 150 °C; (chiplevel)

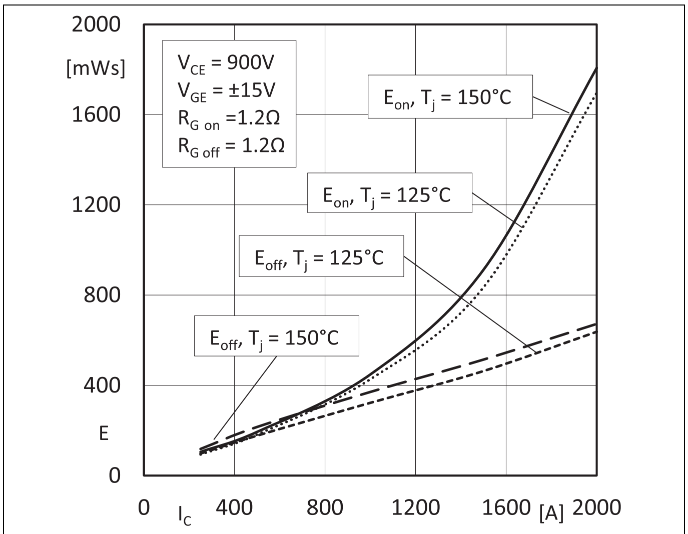


Fig. 3: Switching losses IGBT (typical); $E=f(I_C)$

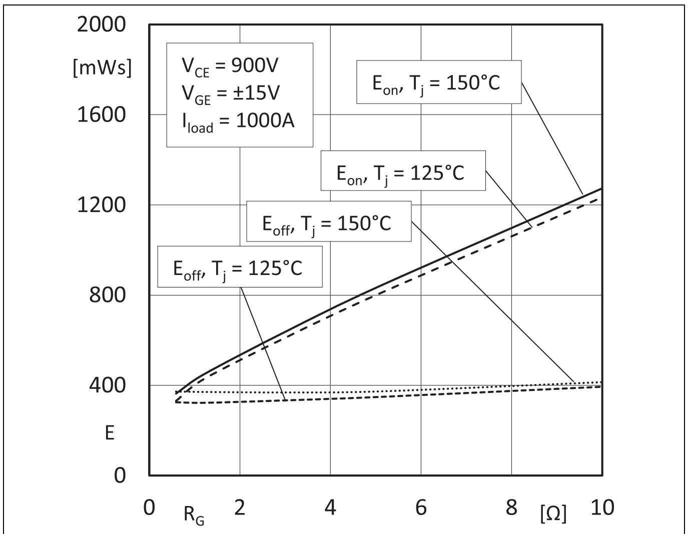


Fig. 4: Switching losses IGBT (typical); $E=f(R_G)$

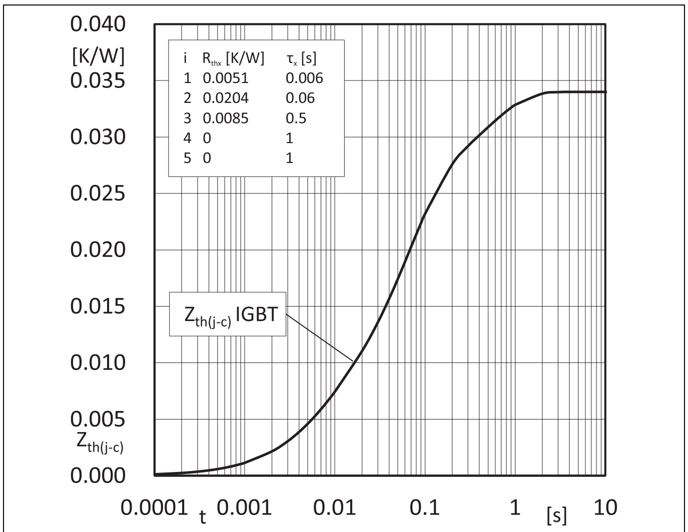


Fig. 5: Transient thermal impedance IGBT

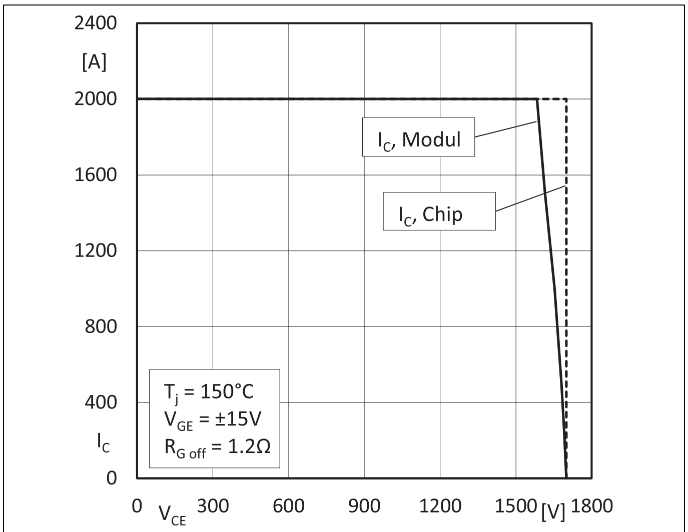


Fig. 6: RBSOA IGBT

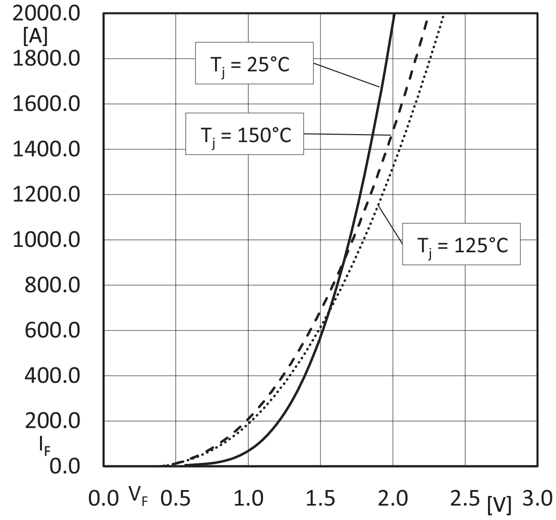


Fig. 7: Forward charact. Diode (typical); I_F=f(V_F); (chiplevel)

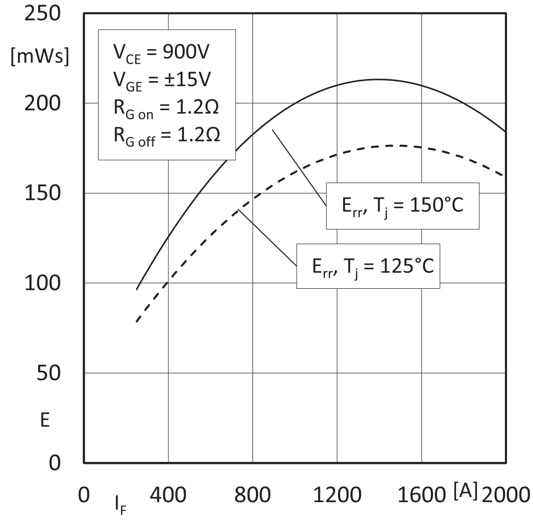


Fig. 8: Switching losses Diode (typical); E=f(I_F)

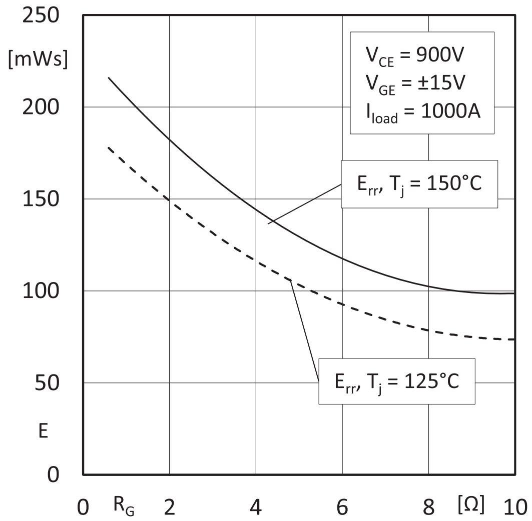


Fig. 9: Switching losses Diode (typical); E=f(R_G)

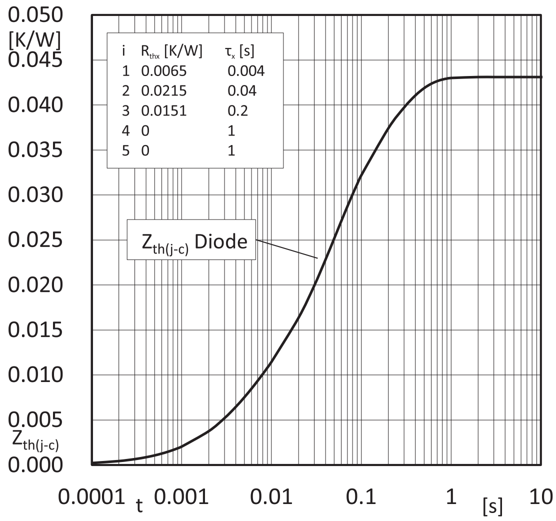


Fig. 10: Transient thermal impedance Diode

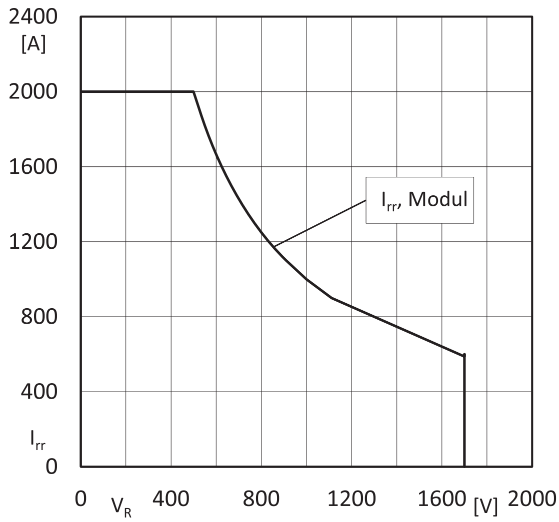


Fig. 11: RBSOA Diode

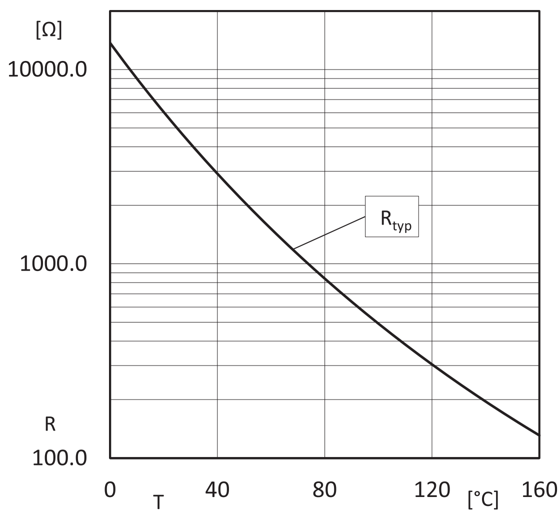


Fig. 12: NTC characteristics (typical)

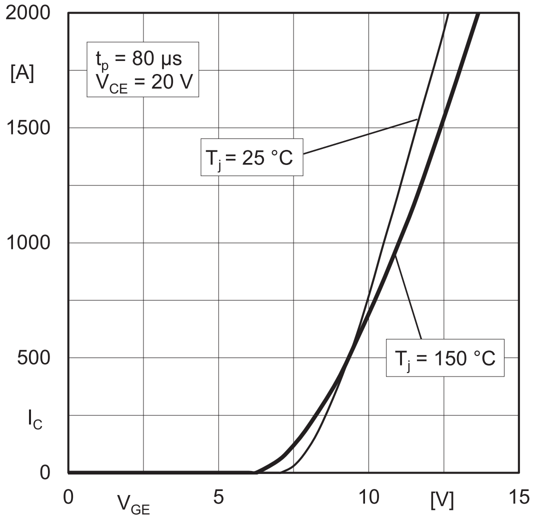


Fig. 13: Typ. transfer characteristic

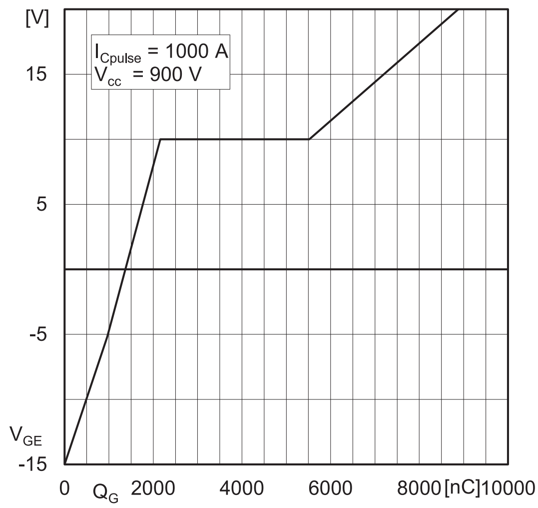
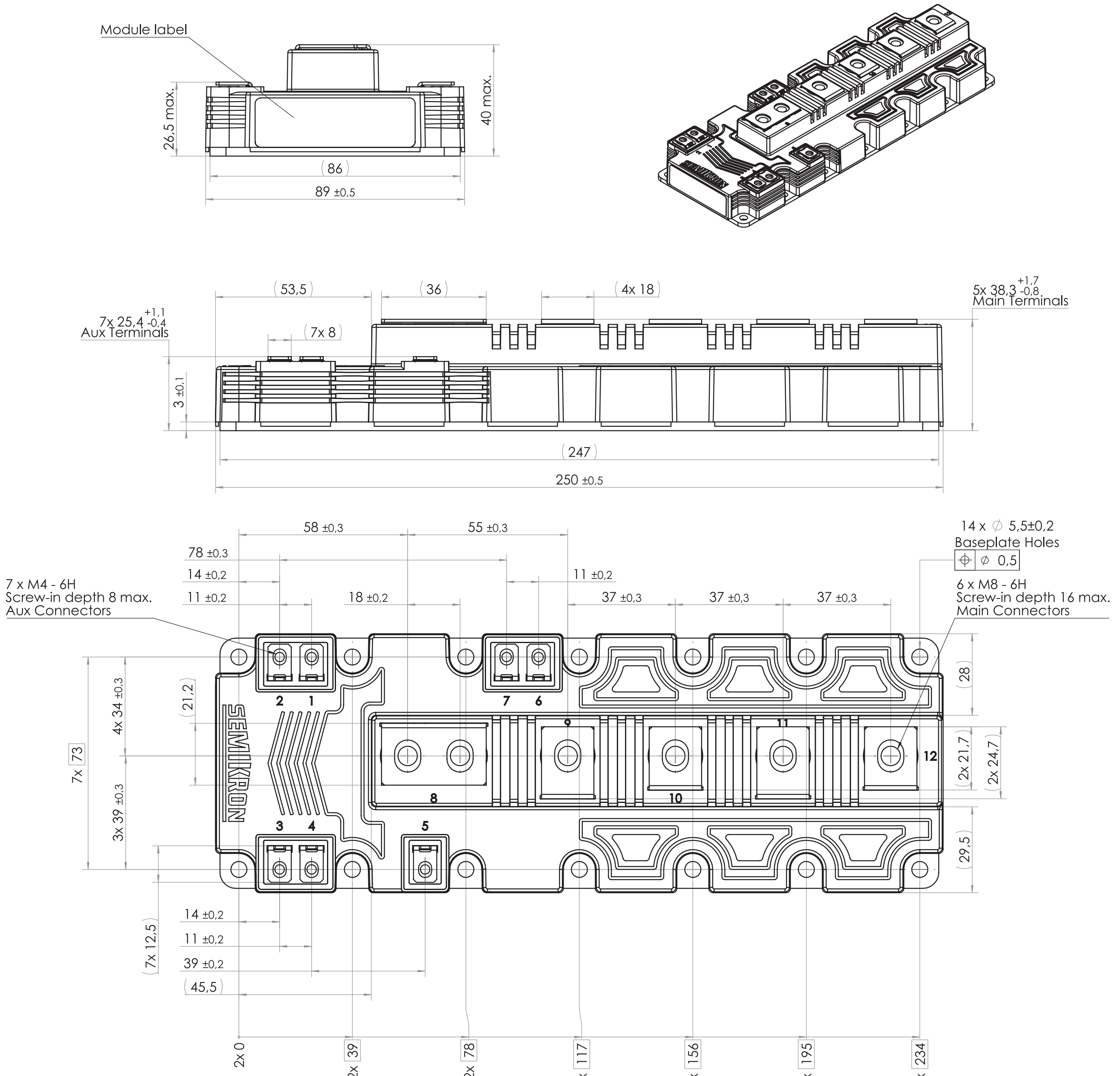


Fig. 14: Typ. gate charge characteristic



• Dimensions in mm
• General tolerances ±0,5mm

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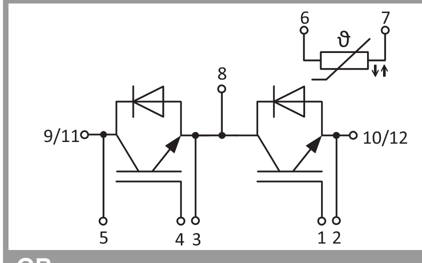

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This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

***IMPORTANT INFORMATION AND WARNINGS**